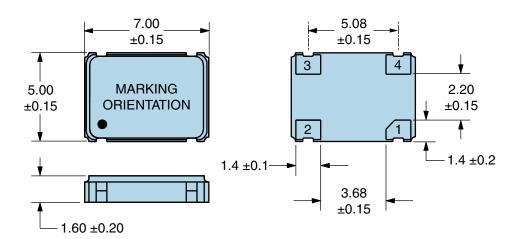


ELECTRICAL SPECIFICATIONS		
Nominal Frequency	3.579545MHz	
Frequency Tolerance/Stability	±50ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over to Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C, Shock, and Vibration)	
Aging at 25°C	±5ppm/year Maximum	
Operating Temperature Range	0°C to +70°C	
Supply Voltage	5.0Vdc ±10%	
Input Current	45mA Maximum (Unloaded)	
Output Voltage Logic High (Voh)	Vdd-0.4Vdc Minimum (IOH = -16mA)	
Output Voltage Logic Low (Vol)	0.4Vdc Maximum (IOL = +16mA)	
Rise/Fall Time	4nSec Maximum (Measured at 20% to 80% of waveform)	
Duty Cycle	50 ±10(%) (Measured at 1.4Vdc with TTL Load or 50% of waveform with HCMOS Load)	
Load Drive Capability	50pF HCMOS Load Maximum	
Output Logic Type	CMOS	
Pin 1 Connection	Tri-State (Disabled Output: High Impedance)	
Pin 1 Input Voltage (Vih and Vil)	+2.0Vdc Minimum to enable output, +0.8Vdc Maximum to disable output, No Connect to enable output.	
Standby Current	50μA Maximum (Pin 1 = Ground)	
Disable Current	30mA Maximum (Pin 1 = Ground)	
Absolute Clock Jitter	250pSec Maximum, ±100pSec Typical	
One Sigma Clock Period Jitter	±50pSec Maximum	
Start Up Time	10mSec Maximum	
Storage Temperature Range	-55°C to +125°C	

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS			
ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V		
Fine Leak Test	MIL-STD-883, Method 1014, Condition A		
Flammability	UL94-V0		
Gross Leak Test	MIL-STD-883, Method 1014, Condition C		
Mechanical Shock	MIL-STD-883, Method 2002, Condition B		
Moisture Resistance	MIL-STD-883, Method 1004		
Moisture Sensitivity	J-STD-020, MSL 1		
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K		
Resistance to Solvents	MIL-STD-202, Method 215		
Solderability	MIL-STD-883, Method 2003		
Temperature Cycling	MIL-STD-883, Method 1010, Condition B		
Vibration	MIL-STD-883, Method 2007, Condition A		



### **MECHANICAL DIMENSIONS (all dimensions in millimeters)**

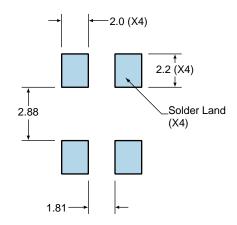


PIN	CONNECTION
1	Tri-State (High Impedance)
2	Ground/Case Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	ECLIPTEK
2	3.5795M
3	PXXYZZ P=Configuration Designator XX=Ecliptek Manufacturing Code Y=Last Digit of the Year ZZ=Week of the Year

#### **Suggested Solder Pad Layout**

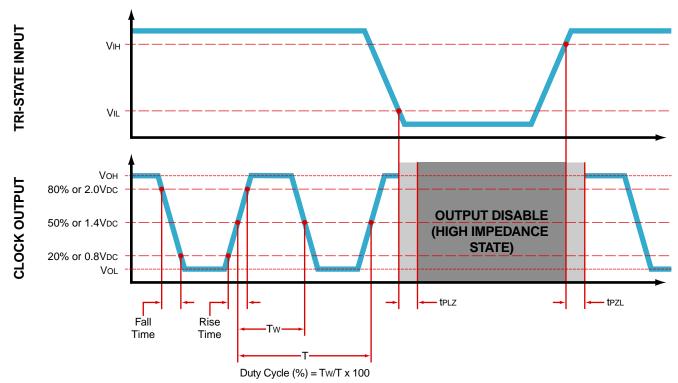
All Dimensions in Millimeters



All Tolerances are ±0.1



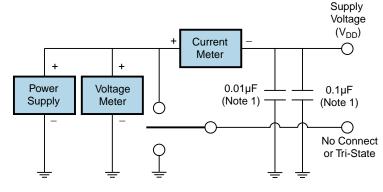
#### **OUTPUT WAVEFORM & TIMING DIAGRAM**

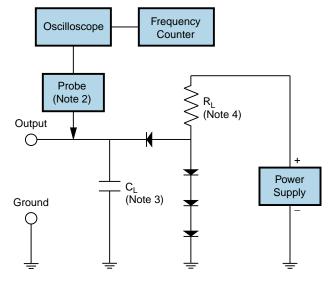


#### **Test Circuit for TTL Output**

Output Load Drive Capability	R <sub>L</sub> Value (Ohms)	C <sub>L</sub> Value (pF)
10TTL	390	15
5TTL	780	15
2TTL	1100	6
10LSTTL	2000	15
1TTL	2200	3

Table 1:  $R_L$  Resistance Value and  $C_L$  Capacitance Value Vs. Output Load Drive Capability





Note 1: An external  $0.1\mu F$  low frequency tantalum bypass capacitor in parallel with a  $0.01\mu F$  high frequency ceramic bypass capacitor close to the package ground and  $V_{DD}$  pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

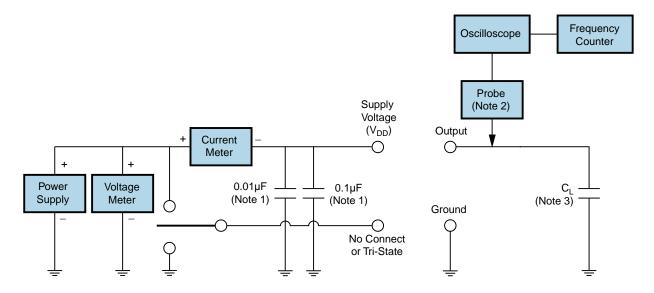
Note 3: Capacitance value  $C_{\mathsf{L}}$  includes sum of all probe and fixture capacitance.

Note 4: Resistance value R<sub>L</sub> is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.



#### **Test Circuit for CMOS Output**



Note 1: An external  $0.1\mu F$  low frequency tantalum bypass capacitor in parallel with a  $0.01\mu F$  high frequency ceramic bypass capacitor close to the package ground and  $V_{DD}$  pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value  $\dot{C}_L$  includes sum of all probe and fixture capacitance.



### **Recommended Solder Reflow Methods**



### **High Temperature Infrared/Convection**

<u> </u>	
T <sub>s</sub> MAX to T <sub>∟</sub> (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T <sub>S</sub> MIN)	150°C
- Temperature Typical (T <sub>s</sub> TYP)	175°C
- Temperature Maximum (T <sub>s</sub> MAX)	200°C
- Time (t <sub>s</sub> MIN)	60 - 180 Seconds
Ramp-up Rate (T <sub>L</sub> to T <sub>P</sub> )	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t∟)	60 - 150 Seconds
Peak Temperature (T <sub>P</sub> )	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T <sub>P</sub> Target)	250°C +0/-5°C
Time within 5°C of actual peak (tp)	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.



### **Recommended Solder Reflow Methods**



#### Low Temperature Infrared/Convection 240°C

T <sub>s</sub> MAX to T <sub>L</sub> (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T <sub>s</sub> MIN)	N/A
- Temperature Typical (T <sub>s</sub> TYP)	150°C
- Temperature Maximum (T <sub>s</sub> MAX)	N/A
- Time (t <sub>s</sub> MIN)	60 - 120 Seconds
Ramp-up Rate (T <sub>L</sub> to T <sub>P</sub> )	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T <sub>P</sub> )	240°C Maximum
Target Peak Temperature (T <sub>P</sub> Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (tp)	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

#### **Low Temperature Manual Soldering**

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

#### **High Temperature Manual Soldering**

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)